

ECE 137 A Mid-Term Exam

Thursday February 5, 2015

Do not open exam until instructed to.

Closed book: Crib sheet and 1 page personal notes permitted

There are 3 problems on this exam, and you have 75 minutes.

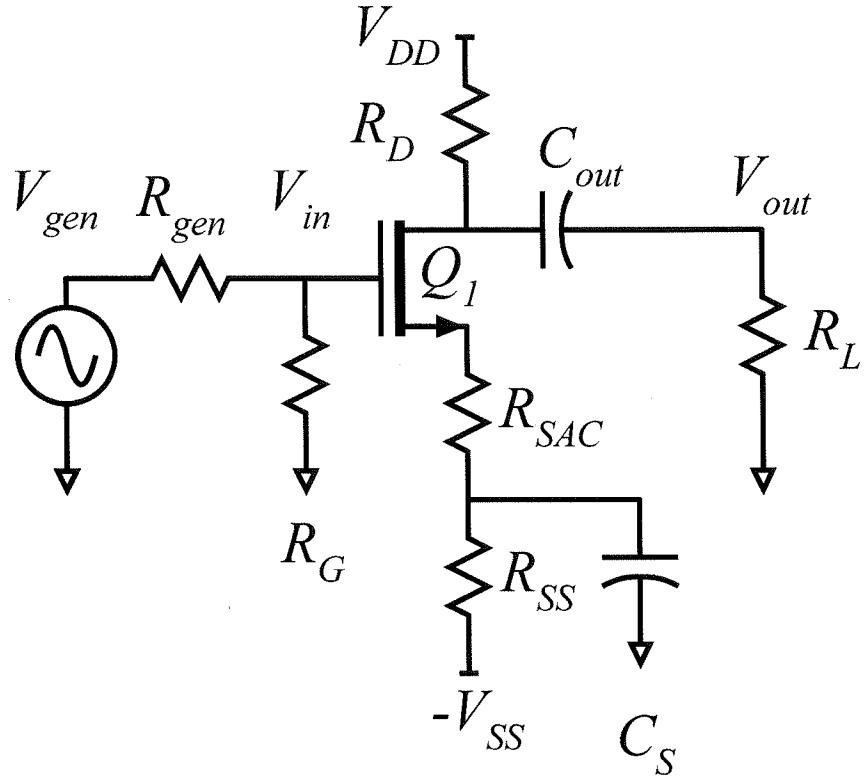
Use any and all reasonable approximations (5% accuracy is fine.),
AFTER STATING and approximately Justifying them.

Name: Solution A

Part	Points Received	Points Possible	Part	Points Received	Points Possible
1a		10	2f		15
1b		5	3a		8
1c		5	3b		8
1d		10	3c		4
1e		15			
2a		10			
2b		5			
2c		5			
2d		10			
2e		5			
TOTAL					100

Problem 1, 30 points

You will be working on the circuit below:



The transistor has

$$L_g = 45\text{nm}, \quad \mu = 400 \text{ cm}^2/\text{V}\cdot\text{s}, \quad \varepsilon_{r,ox} = 3.8, \quad T_{ox} = 1\text{nm}, \quad v_{sat} = 10^7\text{cm/s}, \quad V_{th} = 0.284\text{V},$$

$$1/\lambda = 10\text{V},$$

From which we calculate:

$$c_{ox}v_{sat} = 3.36 \text{ mA/V}/\mu\text{m}, \quad \mu c_{ox} / 2L_g = 15 \text{ mA/V}^2/\mu\text{m}, \quad \Delta V = L_g v_{th} / \mu = 0.113\text{V},$$

The supplies are +1V and -1 V

You are to bias the transistor at 2mA drain current,
with 0.6V DC drain voltage, and with -0.45 V DC source voltage.

$$R_{SAC} = 20\Omega, \quad R_G = 1\text{ M}\Omega, \quad R_{gen} = 75\text{ k}\Omega, \quad R_L = 10\text{k}\Omega$$

C_S and C_{out} are very large (AC short-circuit)

Part a, 10 points

DC bias.

Use this approximation: Ignore (i.e. set to zero) the FET λ parameter in the DC bias calculation.

Find the following:

FET gate width $W_g = \underline{\hspace{2cm}}$ $R_{SS} = \underline{\hspace{2cm}}$ $R_D = \underline{\hspace{2cm}}$

$$V_g = 0V \quad \text{so} \quad V_{GS} = 0.45V \quad \textcircled{1}$$

$\textcircled{1}$ note $V_{EL} + \Delta V = 0.284V + 0.113V = 0.397V$.

$\textcircled{1}$ so we are velocity-limited.

$$V_{EL} + \Delta V/2 = 0.284V + 0.113V/2 = 0.340V$$

$$\textcircled{2} \quad I_D = \frac{3.36 \text{ mA}}{V^2 \cdot \mu\text{m}} \cdot W_g (V_{GS} - 0.340V)$$

$$\textcircled{1} \Rightarrow W_g = \frac{2 \text{ mA}}{\frac{3.36 \text{ mA}}{V^2 \cdot \mu\text{m}}} \cdot \frac{1}{(0.45V - 0.340V)} = 5.41 \mu\text{m}$$

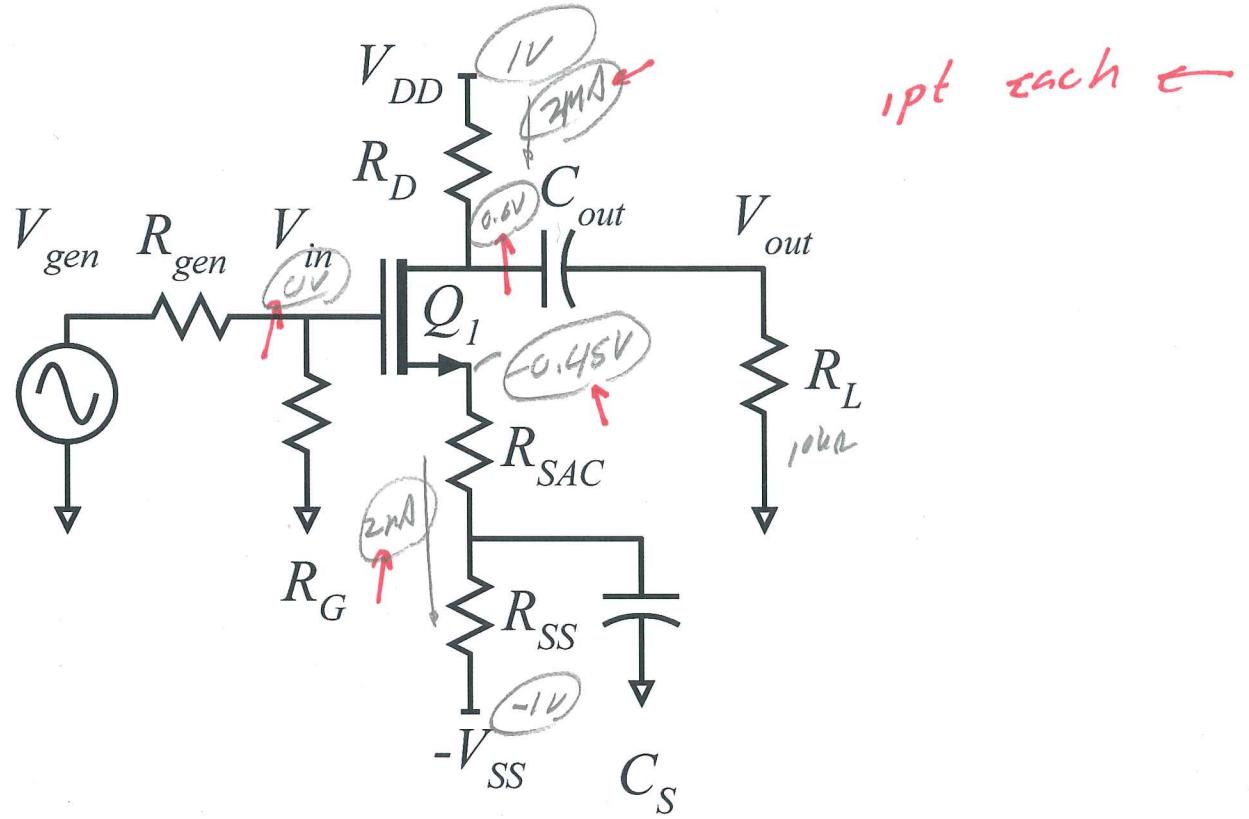
$$\textcircled{2} \quad R_{SS} + R_{SAC} = \frac{IV - 0.45V}{2 \text{ mA}} = \frac{0.55V}{2 \text{ mA}} = 275 \Omega$$

$$R_{SS} = 275 \Omega - 20 \Omega = 255 \Omega$$

$$\textcircled{2} \quad R_D = \frac{IV - 0.6V}{2 \text{ mA}} = \frac{0.4V}{2 \text{ mA}} = 200 \Omega$$

Part b, 5 points

DC bias



On the circuit diagram above, label the DC voltages at **ALL nodes** and the DC currents through **ALL resistors**

Part c, 5 points

Using the actual (nonzero) FET λ parameter, find the FET small signal parameters
 $gm = \underline{\hspace{2cm}}$ $Rds = \underline{\hspace{2cm}}$

velocity limited.

3

$$\begin{aligned} g_m &= v_{sd} C_{ox} W (1 + 1/V_{DS}) \\ &= 3.36 \frac{mS}{\mu A} \cdot 5.4 \mu m \left(1 + \frac{1.05V}{10V} \right) \\ &\approx 18.2 mS (1.105) = 20.1 mS. \end{aligned}$$

2

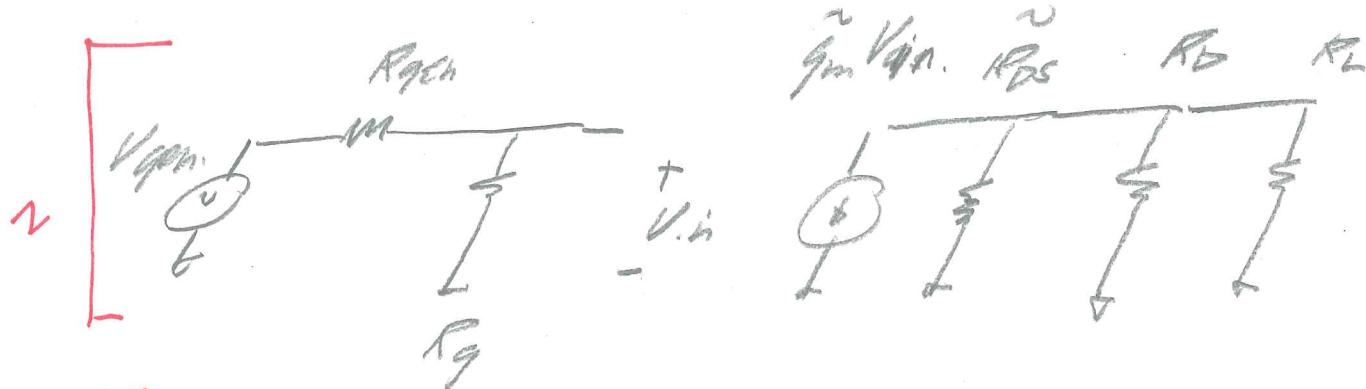
$$R_{DS} = \frac{V_{DS} + V_D}{I_D} \approx \frac{1}{I_D} = \frac{10V}{2mA} = \underline{\underline{5k\Omega}}$$

Part d, 10 points.

Find the small signal voltage gain V_{out}/V_{in} and the amplifier small-signal input resistance.

$$V_{out}/V_{in} = \underline{\hspace{10cm}}$$

$$R_{in, \text{amplifier}} = \underline{\hspace{10cm}}$$



$$2 \quad \boxed{g_m = \frac{1}{1/g_m + R_{SAC}}} = \frac{1}{49\Omega + 20\Omega} = \frac{1}{69\Omega}.$$

$$2 \quad \boxed{R_{DS} = R_{DS}(1 + g_m R_{SAC}) = 5\text{k}\Omega \left(1 + \frac{20\Omega}{49\Omega}\right) = 7.04\text{k}\Omega}$$

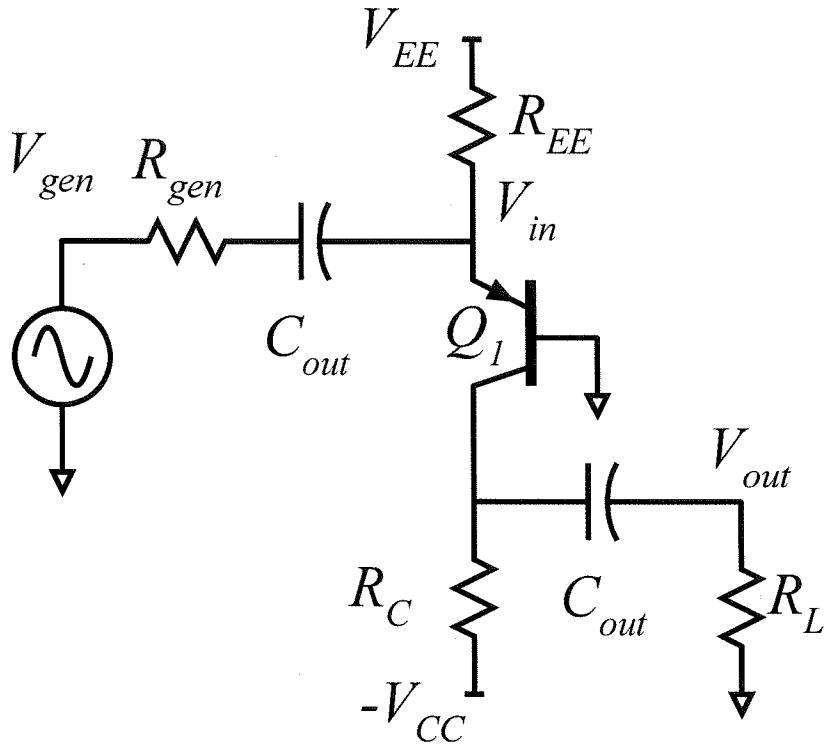
$$1 \quad \boxed{R_{reg} = R_{DS} // R_D // R_L = 7.04\text{k}\Omega // 200\text{m}\Omega // 10\text{k}\Omega = 191\Omega}$$

$$2 \quad \boxed{v_o/v_{in} = -g_m R_{reg} = -\frac{191}{69\Omega} = -2.76}$$

$$1 \quad \boxed{R_{in, \text{amp}} = R_g = 1\text{M}\Omega}$$

Problem 2, 50 points

You will be working on the circuit below:



Q1: $\beta = 100$, $V_A = \infty$ V

The supplies are +5V and -5 V.

You will bias the transistor with 2mA collector current.

The DC collector bias voltage is -2.5V.

R_L is $10\text{k}\Omega$, R_{gen} is $100\ \Omega$

Part a, 10 points

DC bias.

Find the following:

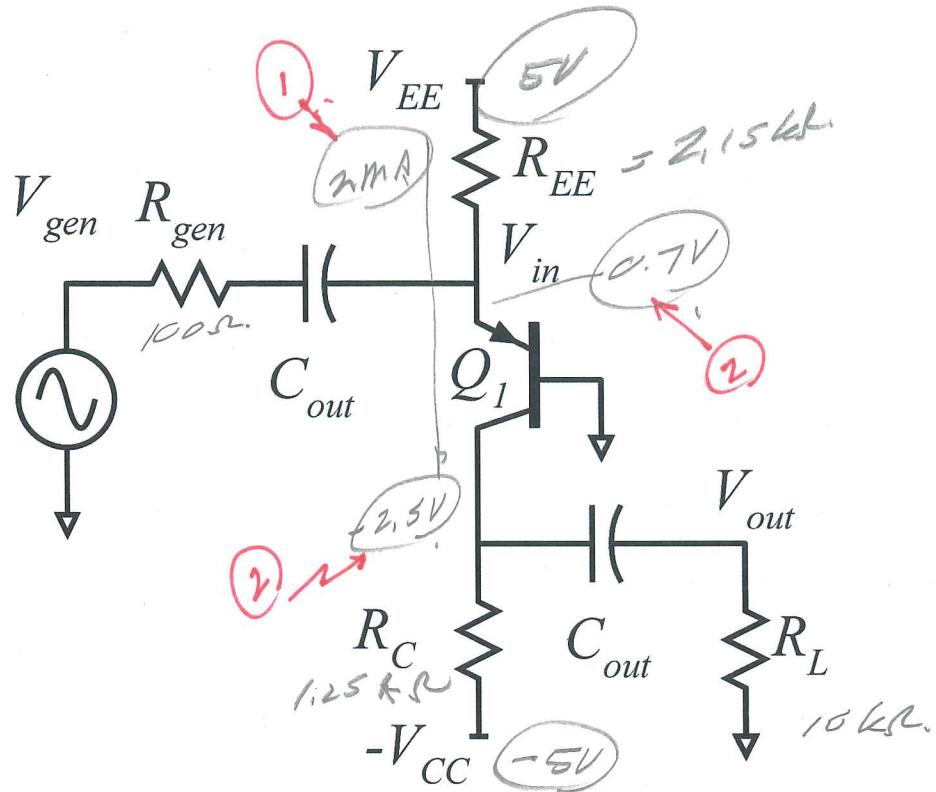
$$R_{EE} = \underline{\hspace{2cm}} \quad R_C = \underline{\hspace{2cm}}$$

5.
$$R_{EE} = \frac{5V - 0.7V}{2mA} = \frac{4.3V}{2mA} = 2.15k\Omega$$

5.
$$R_C = \frac{5V - 2.5V}{2mA} = \frac{2.5V}{2mA} = 1.25k\Omega$$

Part b, 5 points

DC bias



On the circuit diagram above, label the DC voltages at **ALL nodes** and the DC currents through **ALL resistors**

Part c, 5 points

Find the small signal parameters of Q1.

$$gm = \underline{\hspace{2cm}} \quad R_{ce} = \underline{\hspace{2cm}} \quad R_{be} = \underline{\hspace{2cm}}$$

2.
$$g_m = \frac{2mA}{26mV} = \frac{1}{f_{3dB}} = 76.9 \text{ mS.}$$

1.
$$R_{ce} = \frac{V_o + V_A}{I_C} = \infty$$

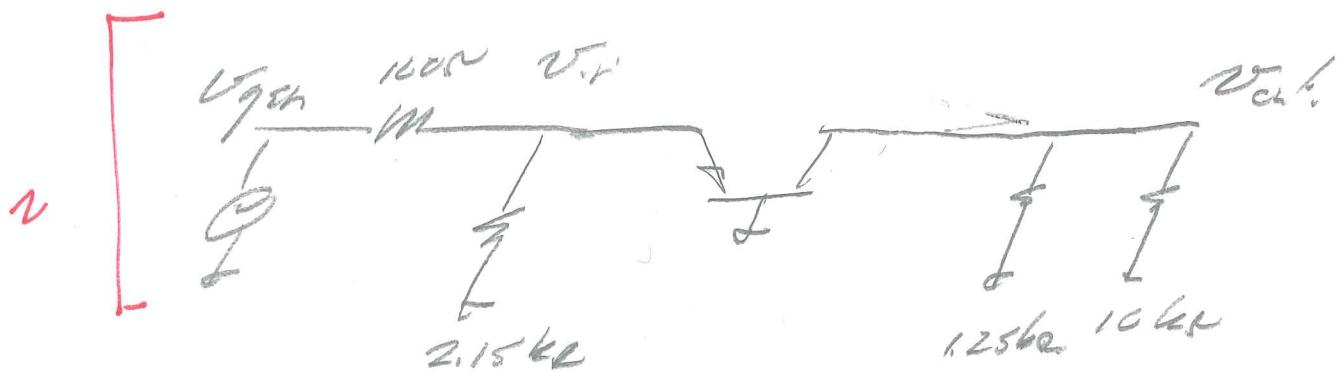
2.
$$R_{ce} = \beta/g_m = 100 \cdot 13\Omega = 1.3 \text{ k}\Omega$$

Part d, 10 points.

Find the small signal voltage gain (V_{out}/V_{in}) of Q1 and the amplifier small-signal input resistance.

$V_{out}/V_{in} =$ _____

$R_{in,amp} =$ _____



2 $R_{eq} = 10k\Omega \parallel 1.25k\Omega = 1.11k\Omega$

2 $R_{in} = \left(\frac{1}{g_m} + \frac{R_b}{B} \right) \left(\frac{R_e + R_{eq}}{R_{ce}} \right) = \frac{1}{g_m} = 13.2 \Omega$

2 $A = \frac{V_{out}}{V_{in}} = g_m R_{eq} = \frac{1.11k\Omega}{13.2} = 85.5$

2. $R_{in,amp} = R_{in} \parallel 2.15k\Omega = 13.2 \parallel 2.15k\Omega \approx 13.1 \Omega$

Part e, 5 points

Find (V_{in}/V_{gen}) and (V_{out}/V_{gen})

$$(V_{in}/V_{gen}) = \underline{\hspace{2cm}}$$

$$(V_{out}/V_{gen}) = \underline{\hspace{2cm}}$$

3 [$\frac{V_{in}}{V_{gen}} = \frac{R_{in}}{R_{in} + R_{gen}} = \frac{13\Omega}{13\Omega + 100\Omega} = 0.115$]

2 [$\frac{V_o}{V_{gen}} = 0.115 \cdot 85.5 = 9.84$]

Part f, 15 points

Now you must find the maximum signal swings. Find the output voltage due to saturation and cutoff in Q2. *Give the sign (+ or -) in your answers below.*

Cutoff of Q1; Maximum ΔV_{out} resulting = _____

Saturation of Q1; Maximum ΔV_{out} resulting = _____

cutoff $I_{CQ} = 2 \text{ mA}$, $I_{m1} = 0 \text{ mA}$] 4
 $\Delta I_C / I_{max} = 2 \text{ mA}$; decrease.

$$\Delta V_{out} = 2 \text{ mA} \cdot R_{load} = 2 \text{ mA} \cdot 1.11 \text{ k}\Omega$$

= 2.22 Volts, negative] 4

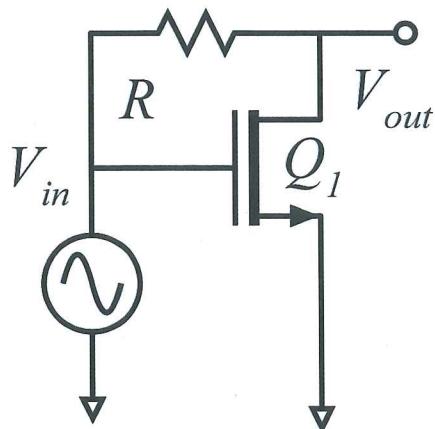
Saturation

3 [$V_{CEQ} = 3.2V$

3 [$V_{CESsat} \approx 0.5V$

1 [$\Delta V_{out} = 2.7V$. positive

Problem 3, 20 points
nodal analysis



You will be working on the circuit to the left.

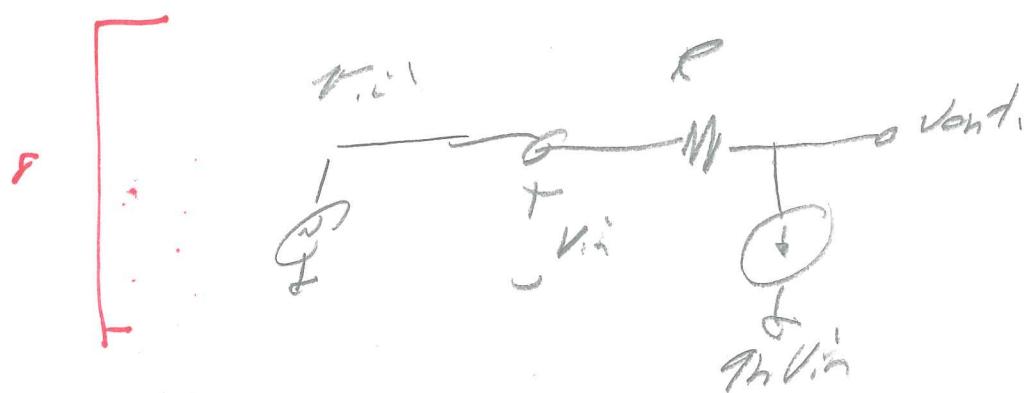
Ignore DC bias analysis. You don't need it.

Transistor 1 has transconductance gm_1 .

The drain-source resistances R_{ds} of the transistor is infinity (so you don't need to draw it!)

Part a, 8 points

Draw the small-signal equivalent circuit



*take off 1/3 pts if controlling voltage
not shown.*

Part b, 8 points

Find, by nodal analysis, a small-signal expression for V_{out}/V_{in} .

$V_{out}/V_{in} = \underline{\hspace{10mm}}$

4pts. $\boxed{ZI = 0 @ V_{out}}$

$$g_m V_{in} + \frac{V_{out} - V_{in}}{R} = 0.$$

$$(g_m - 1/R)V_{in} + V_{out}/R = 0$$

$$\frac{V_{out}}{V_{in}} = -\frac{(g_m - 1/R)}{1/R} = -g_m R + 1$$

4pts.

$$\boxed{\frac{V_{out}}{V_{in}} = 1 - g_m R}$$

Part c, 4 points

$$gm_1 = 1 \text{ mS}, R = 4 \text{kOhm}$$

Give a numerical value for V_{out}/V_{in} .

$$V_{out}/V_{in} = \underline{\hspace{2cm}}$$

$$\begin{aligned} 4. \quad \frac{V_o}{V_i} &= 1 - g_m R \\ &= 1 - 1 \text{ mS} (8 \text{k}\Omega) \\ &= -2 \end{aligned}$$